

### Main product characteristics

$I_{F(AV)}$	2 x 20 A
$V_{RRM}$	120 V
$T_{j(max)}$	175° C
$V_{F(typ)}$	0.57 V

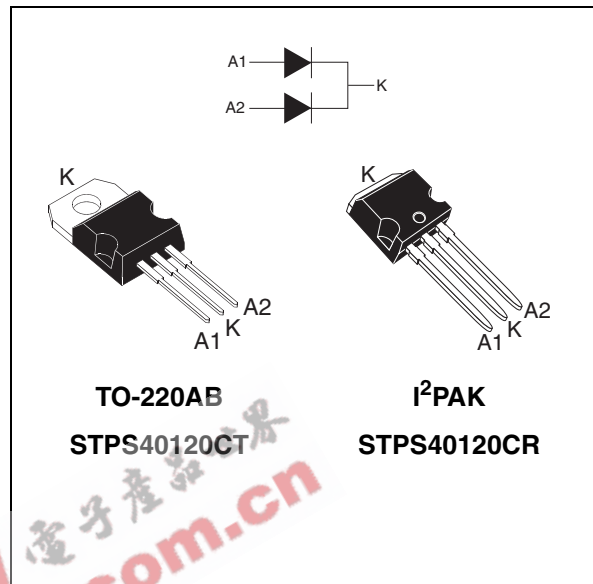
### Feature and benefits

- High junction temperature capability
- Avalanche rated
- Low leakage current
- Good trade-off between leakage current and forward voltage drop

### Description

Dual center tap Schottky rectifier suited for high frequency Switch Mode Power Supply.

Packaged in TO-220AB and I<sup>2</sup>PAK, this device is intended to be used in notebook and LCD adaptors, desktop SMPS, providing in these applications a margin between the remaining voltages applied on the diode and the voltage capability of the diode.



### Order code

Part Number	Marking
STPS40120CT	STPS40120CT
STPS40120CR	STPS40120CR

**Table 1. Absolute ratings (limiting values, per diode)**

Symbol	Parameter		Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage		120	V	
$I_{F(RMS)}$	RMS forward current		30	A	
$I_{F(AV)}$	Average forward current	$\delta = 0.5$ $T_c = 145^\circ \text{C}$	Per diode 40	A	
$I_{FSM}$	Surge non repetitive forward current		$t_p = 10 \text{ ms}$ Sinusoidal	200	A
$P_{ARM}$	Repetitive peak avalanche power		$t_p = 1 \mu\text{s}$ $T_j = 25^\circ \text{C}$	10500	W
$T_{stg}$	Storage temperature range		-65 to + 175	° C	
$T_j$	Maximum operating junction temperature <sup>(1)</sup>		175	° C	

1.  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  condition to avoid runaway for a diode on its own heatsink

# 1 Characteristics

**Table 2. Thermal parameters**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.6	° C/W
		Total	0.85	
$R_{th(c)}$	Coupling	Total	0.1	° C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

**Table 3. Static electrical characteristics (per diode)**

Symbol	Test conditions			Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			25	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$			4	12	mA
$V_F^{(2)}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 7.5\text{ A}$			0.73	V
		$T_j = 125^\circ\text{C}$			0.57	0.61	
		$T_j = 25^\circ\text{C}$	$I_F = 20\text{ A}$			0.9	
		$T_j = 125^\circ\text{C}$			0.69	0.73	
		$T_j = 25^\circ\text{C}$	$I_F = 40\text{ A}$			1	
		$T_j = 125^\circ\text{C}$			0.83	0.88	

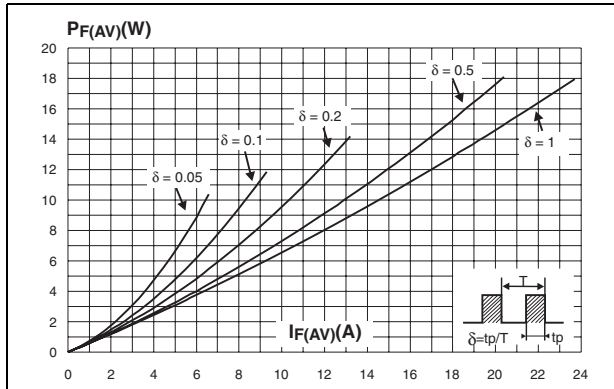
1. Pulse test :  $t_p = 5\text{ ms}$ ,  $\delta < 2\%$

2. Pulse test :  $t_p = 380\text{ }\mu\text{s}$ ,  $\delta < 2\%$

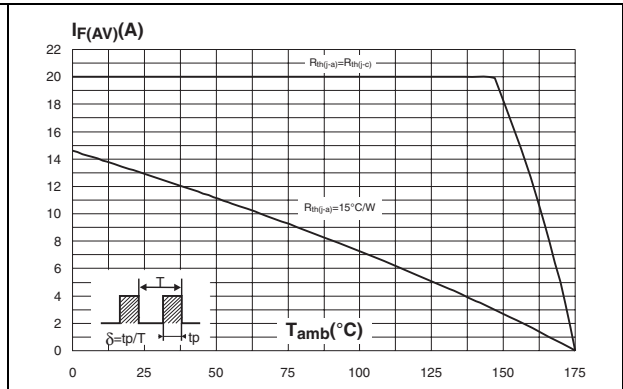
To evaluate the maximum conduction losses use the following equation :

$$P = 0.58 \times I_{F(AV)} + 0.0075 I_F^2 (\text{RMS})$$

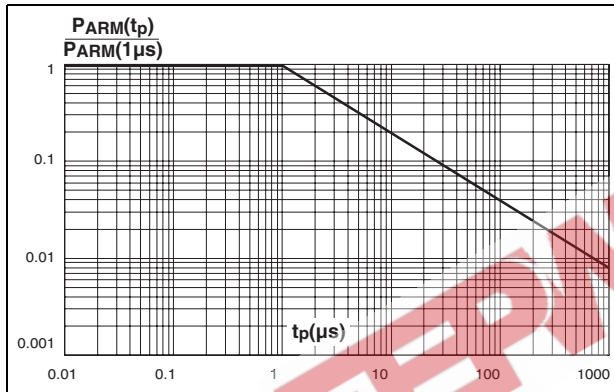
**Figure 1. Average forward power dissipation versus average forward current (per diode)**



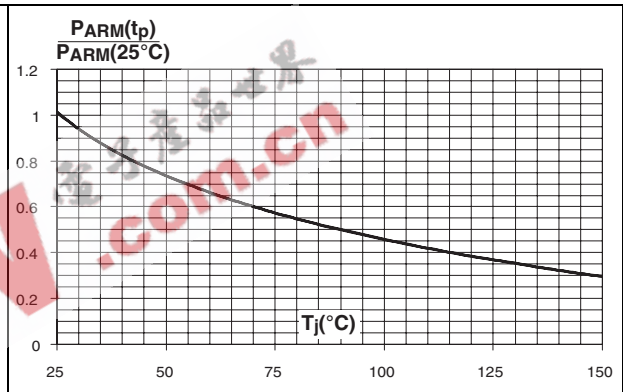
**Figure 2. Average forward current versus ambient temperature ( $\delta = 0.5$ , per diode)**



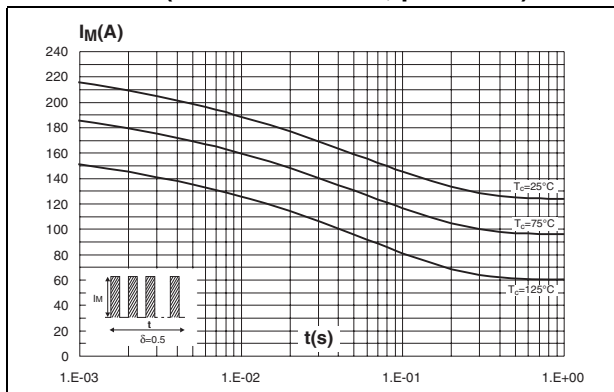
**Figure 3. Normalized avalanche power derating versus pulse duration**



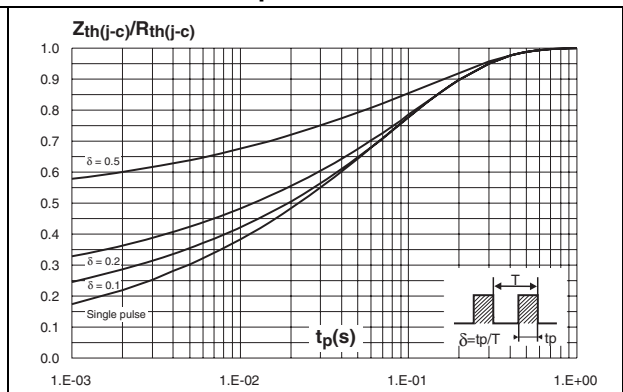
**Figure 4. Normalized avalanche power derating versus junction temperature**



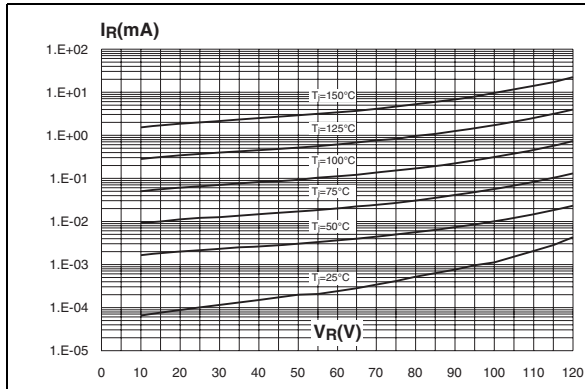
**Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)**



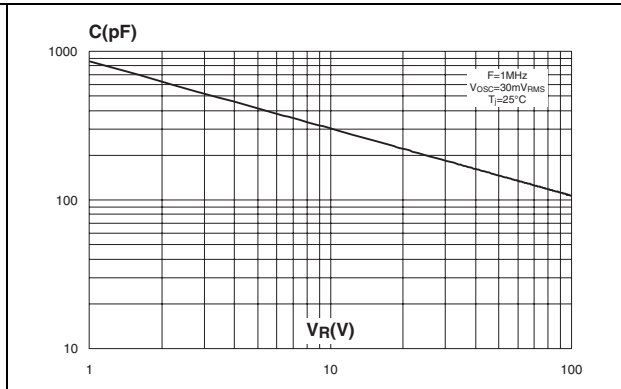
**Figure 6. Relative variation of thermal impedance junction to ambient versus pulse duration**



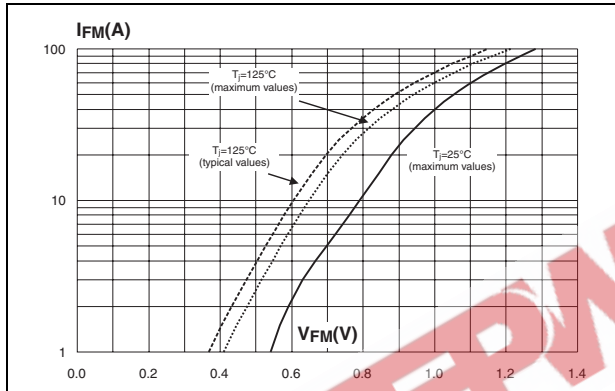
**Figure 7. Reverse leakage current versus reverse voltage applied (typical values, per diode)**



**Figure 8. Junction capacitance versus reverse voltage applied (typical values, per diode)**



**Figure 9. Forward voltage drop versus forward current (per diode)**



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## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 Nm
- Maximum torque value: 1.0 Nm

Figure 10. TO-220AB dimensions

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

Table 4. I<sup>2</sup>PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com).

### 3 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS40120CT	STPS40120CT	TO-220AB	2.23 g	50	Tube
STPS40120CR	STPS40120CR	I <sup>2</sup> PAK	1.49 g	50	Tube

### 4 Revision history

Date	Revision	Description of Changes
18-Feb-2005	1	First issue
1-Dec-2006	2	Reformatted to current standards. Added I <sup>2</sup> PAK.

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